

Docket No. 202450US0

IN RE APPLICATION OF Atsushi SHIOTA, et al.

SERIAL NO. 09 770,289

FILED January 29, 2001

FOR: PROCESS FOR PRODUCING SILICA-BASED FILM, SILICA-BASED FILM, INSULATING FILM, AND SEMICONDUCTOR DEVICE

ASSISTANT COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231

SIR:



Transmitted herewith is an Amendment w/ Marked Up Copy (7) in the above-identified application.

- No additional fee is required
- Small entity status of this application under 37 C.F.R. §1.9 and §1.27 is claimed.
- Additional documents filed herewith:

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TC 1700

The Fee has been calculated as shown below:

CLAIMS	CLAIMS REMAINING		HIGHEST NUMBER PREVIOUSLY PAID	NO. EXTRA CLAIMS	RATE	CALCULATIONS
TOTAL	16	MINUS	20	0	× \$18 =	\$0.00
INDEPENDENT	1	MINUS	1	0	× \$84 =	\$0.00
		<input type="checkbox"/> MULTIPLE DEPENDENT CLAIMS			+ \$280 =	\$0.00
						TOTAL OF ABOVE CALCULATIONS
		<input type="checkbox"/> Reduction by 50% for filing by Small Entity				\$0.00
		<input type="checkbox"/> Recordation of Assignment			+ \$40 =	\$0.00
						TOTAL
						\$0.00

A check in the amount of \$0.00 is attached.

- Please charge any additional Fees for the papers being filed herewith and for which no check is enclosed herewith, or credit any overpayment to deposit Account No. 15-0030. A duplicate copy of this sheet is enclosed.
- If these papers are not considered timely filed by the Patent and Trademark Office, then a petition is hereby made under 37 C.F.R. §1.136, and any additional fees required under 37 C.F.R. §1.136 for any necessary extension of time may be charged to Deposit Account No. 15-0030. A duplicate copy of this sheet is enclosed.

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202450US0



IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF:

ATSUSHI SHIOTA ET AL. : GROUP ART UNIT: 1712

SERIAL NO: 09/770,289 :

FILED: JANUARY 29, 2001 : EXAMINER: FEELY, M.

FOR: PROCESS FOR PRODUCING  
SILICA-BASED FILM, SILICA-  
BASED FILM, INSULATING FILM,  
AND SEMICONDUCTOR DEVICE

AMENDMENT

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MAY 23 2002

ASSISTANT COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231

**TC 1700**

SIR:

In response to the Office Action dated February 28, 2002, please amend the application identified above as follows (marked-up copy of amendments attached):

IN THE CLAIMS

Please amend Claims 1, 3 and 6 as follows:

1. (Amended) A process for producing a silica-based film, the process comprising irradiating a film comprising at least one siloxane compound with electron beams at an irradiation dose of from 1 to 500  $\mu\text{C cm}^2$  to thereby convert the film into a film having a dielectric constant of 3 or lower and having silicon carbide bonds represented by Si-C-Si.